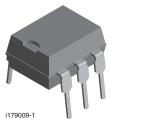
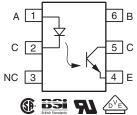
MOC8101, MOC8102, MOC8103, MOC8104, MOC8105

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Optocoupler, Phototransistor Output, no Base Connection





FEATURES

- Isolation test voltage, 5300 V_{RMS}
- No base terminal connection for improved common mode interface immunity



- · Industry standard dual in line package
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC





RoHS COMPLIANT

DESCRIPTION

The MOC8101, MOC8102, MOC8103, MOC8104, MOC8105 family optocoupler consisting of a gallium arsenide infrared emitting diode optically coupled to a silicon planar phototransistor detector in a plastic plug-in DIP-6 package.

The coupling device is suitable for signal transmission between two electrically separated circuits. The potential difference between the circuits to be coupled should not exceed the maximum permissible reference voltages.

The base terminal of the MOC8101, MOC8102, MOC8103, MOC8104, MOC8105 is not connected, resulting in a substantially improved common mode interference immunity.

AGENCY APPROVALS

- UL1577, file no. E52744 system code H or J, double protection
- CSA 93751
- BSI IEC 60950; IEC 60065
- DIN EN 60747-5-5 (VDE 0884) available with option 1

ORDERING INFORMATIO	N						
M O C 8 1 0 # - # X 0 # # T PART NUMBER CTR PACKAGE OPTION TAPE AND REEL Option 7 Option 9 Option 7 Option 9							
AGENCY CERTIFIED/PACKAGE	CTR (%)						
AGENOT GENTINED/T AGRAGE	10 mA						
UL, CSA, BSI	50 to 80	73 to 117	108 to 173	160 to 256	65 to 133		
DIP-6	MOC8101	MOC8102	MOC8103	MOC8104	MOC8105		
DIP-6, 400 mil, option 6	=	MOC8102-X006	-	-	=		
SMD-6, option 9	MOC8101-X009	MOC8102-X009	-	-	=		
VDE, UL, CSA, BSI	50 to 80	73 to 117	108 to 173	160 to 256	65 to 133		
DIP-6	MOC8101-X001	-	MOC8103-X001	-	-		
DIP-6, 400 mil	-	MOC8102-X016	-	MOC8104-X016	-		
SMD-6, option 7	MOC8101-X017T	MOC8102-X017T	-	-	=		
SMD-6, option 9	-	-	-	MOC8104-X019T	=		

Note

• Additional options may be possible, please contact sales office.



MOC8101, MOC8102, MOC8103, MOC8104, MOC8105

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ABSOLUTE MAXIMUM RAT	NGS (T _{amb} = 25 °C, unless other	wise specified)	
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT	·		•	
Reverse voltage		V _R	6.0	V
Forward continuous current		l _F	60	mA
Surge forward current	t ≤ 10 µs	I _{FSM}	2.5	Α
Power dissipation		P _{diss}	100	mW
Derate linearly from 25°C			1.33	mW/°C
OUTPUT	,		•	
Collector emitter breakdown voltage		BV _{CEO}	30	V
Emitter collector breakdown voltage		BV _{ECO}	7.0	V
Collector current		I _C	50	mA
Derate linearly from 25°C			2.0	mW/°C
Power dissipation		P _{diss}	150	mW
COUPLER	,		•	
Isolation test voltage		V _{ISO}	5300	V_{RMS}
O			≥ 7.0	mm
Creepage distance			8.0 ⁽²⁾	mm
Clearance distance			≥ 7.0	mm
Clearance distance			8.0 ⁽²⁾	mm
Isolation thickness between emitter and detector			≥ 0.4	mm
Comparative tracking index per DIN IEC 112/VDE 0303, part 1		СТІ	175	
Isolation resistance	V _{IO} = 500 V	R _{IO}	10 ¹²	Ω
Derate linearly from 25 °C	-	-	3.33	mW/°C
Total power dissipation		P _{tot}	250	mW
Storage temperature		T _{stg}	- 55 to + 150	°C
Operating temperature		T _{amb}	- 55 to + 100	°C
Junction temperature		T _i	100	°C
Soldering temperature (1)	max. 10 s, dip soldering: distance to seating plane ≥ 1.5 mm	T _{sld}	260	°C

Notes

⁽²⁾ Applies to wide bending option 6.

PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT						•	
Forward voltage	I _F = 10 mA		V _F		1.25	1.5	V
Breakdown voltage	$I_R = 10 \mu A$		V_{BR}	6.0			V
Reverse current	V _R = 6.0 V		I _R		0.01	10	μA
Capacitance	V _R = 0 V, f = 1.0 MHz		Co		25		pF
Thermal resistance			R _{thja}		750		K/W
OUTPUT							
Collector emitter capacitance	V _{CE} = 5.0 V, f = 1.0 MHz		C _{CE}		5.2		pF
Calleston and Atlantale de de la compant	V _{CE} = 10 V, T _{amp} = 25 °C	MOC8101	I _{CEO1}		1.0	50	nA
Collector emitter dark current	V _{CE} = 10 V, T _{amp} = 100 °C	MOC8102	I _{CEO1}	1	1.0		μA
Collector emitter breakdown voltage	I _C = 1.0 mA		BV _{CEO}	30			V
Emitter collector breakdown voltage	I _E = 100 μA		BV _{ECO}	7.0			V
Thermal resistance			R _{thja}		500		K/W
COUPLER		•					
Saturation voltage collector emitter	$I_F = 5.0 \text{ mA}$		V_{CEsat}		0.25	0.4	V
Coupling capacitance			C _C		0.6		рF

Note

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not
implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute
maximum ratings for extended periods of the time can adversely affect reliability.

⁽¹⁾ Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.



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CURRENT TRANSFER RATIO (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Current transfer ratio	V _{CE} = 10 V, I _F = 10 mA	MOC8101	CTR	50		80	%	
		MOC8102	CTR	73		117	%	
		MOC8103	CTR	108		173	%	
		MOC8104	CTR	160		256	%	
		MOC8105	CTR	65		133	%	

SWITCHING CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	SYMBO L	MIN.	TYP.	MAX.	UNIT		
Turn-on time	V_{CC} = 10 V, I_{C} = 2.0 mA, R_{L} = 100 Ω	t _{on}		3.0		μs		
Turn-off time	V_{CC} = 10 V, I_{C} = 2.0 mA, R_{L} = 100 Ω	t _{off}		2.3		μs		
Rise time	V_{CC} = 10 V, I_{C} = 2.0 mA, R_{L} = 100 Ω	t _r		2.0		μs		
Fall time	V_{CC} = 10 V, I_{C} = 2.0 mA, R_{L} = 100 Ω	t _f		2.0		μs		
Cut off frequency		f _{co}		250		kHz		

TYPICAL CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

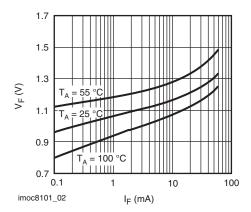


Fig. 1 - Forward Voltage vs. Forward Current

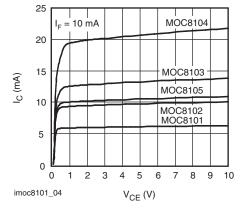


Fig. 3 - Collector Current vs. Collector Emitter Voltage

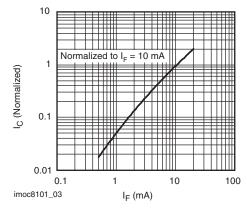


Fig. 2 - Collector Current vs. LED Forward Current

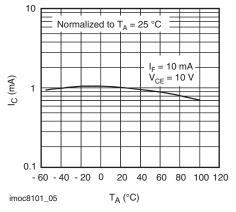


Fig. 4 - Collector Current vs. Ambient Temperature

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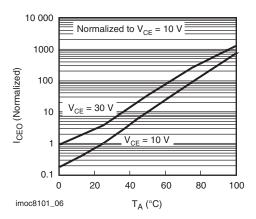


Fig. 5 - Collector Emitter Dark Current vs. Ambient Temperature

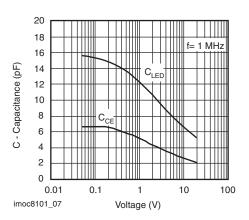


Fig. 6 - Capacitance vs. Voltage

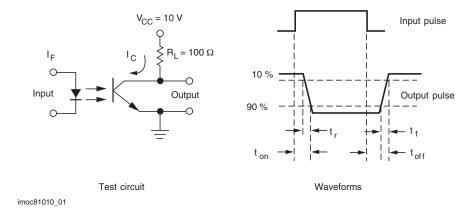


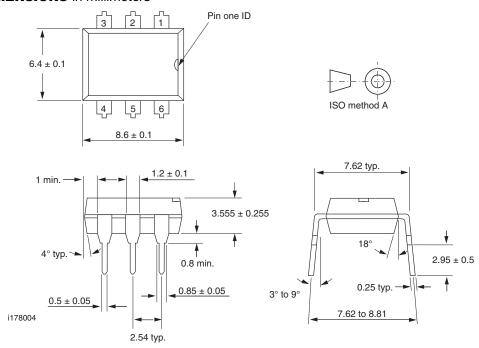
Fig. 7 - Switching Time Test Circuit and Waveforms

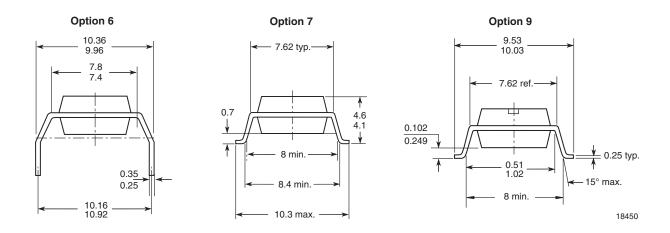


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PACKAGE DIMENSIONS in millimeters

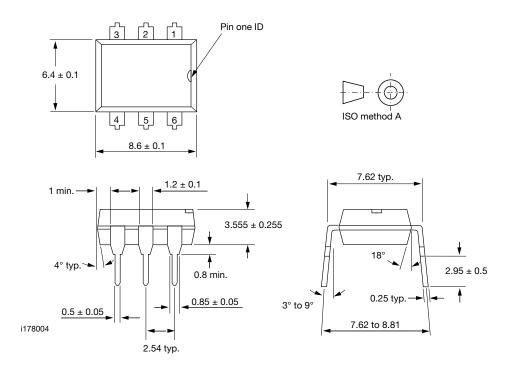






DIP-6A

PACKAGE DIMENSIONS in inches (millimeters)



Note

The information in this document provides generic information but for specific information on a product the appropriate product datasheet should be used.



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